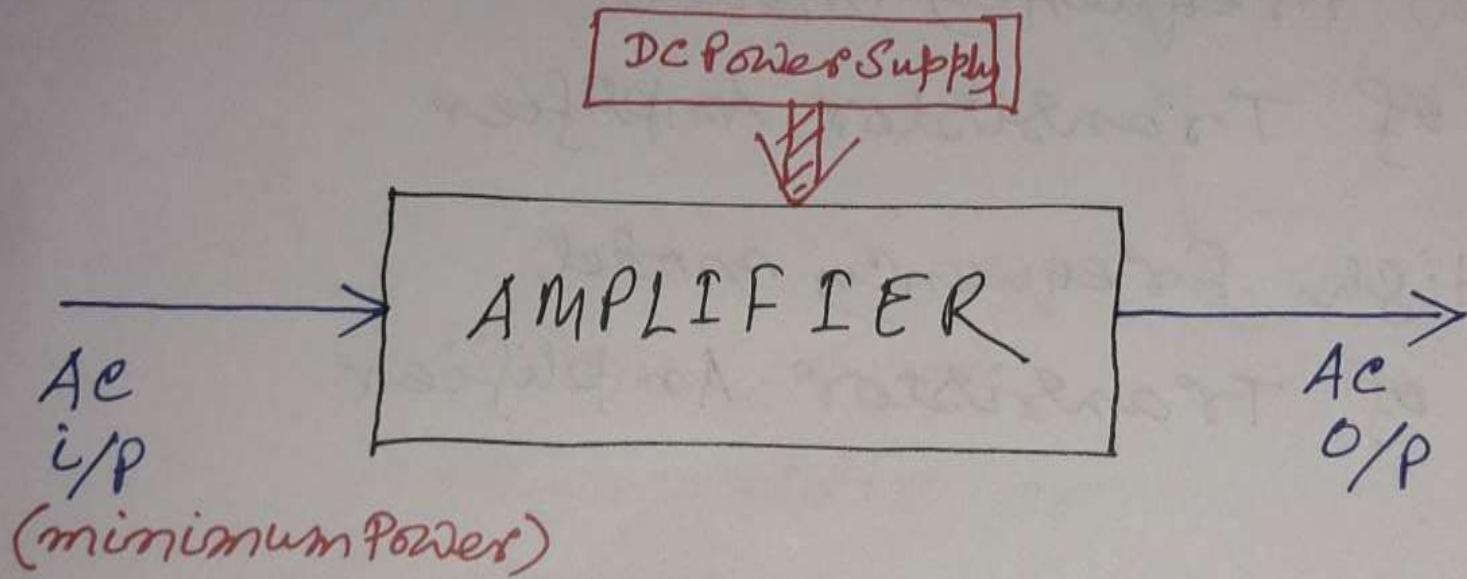


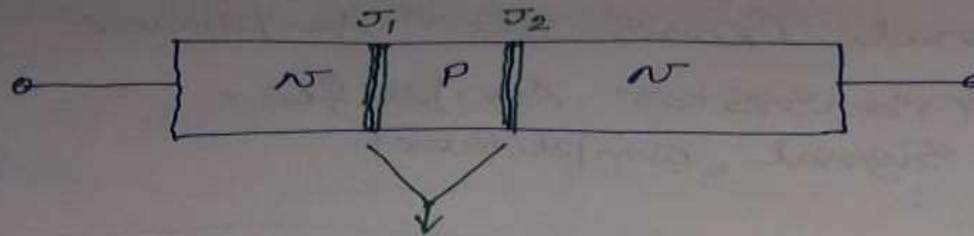
# Transistor Amplifier

# Transistor Amplifier

Transistor as an AMPLIFIER



# Transistor Amplifier



$$X_C = \frac{1}{2\pi f C}$$

At low frequencies  
 $X_C \rightarrow$  high  
(so may be neglected)

At high frequencies  
 $X_C \rightarrow$  low  
(cannot be neglected)

# Transistor Amplifier

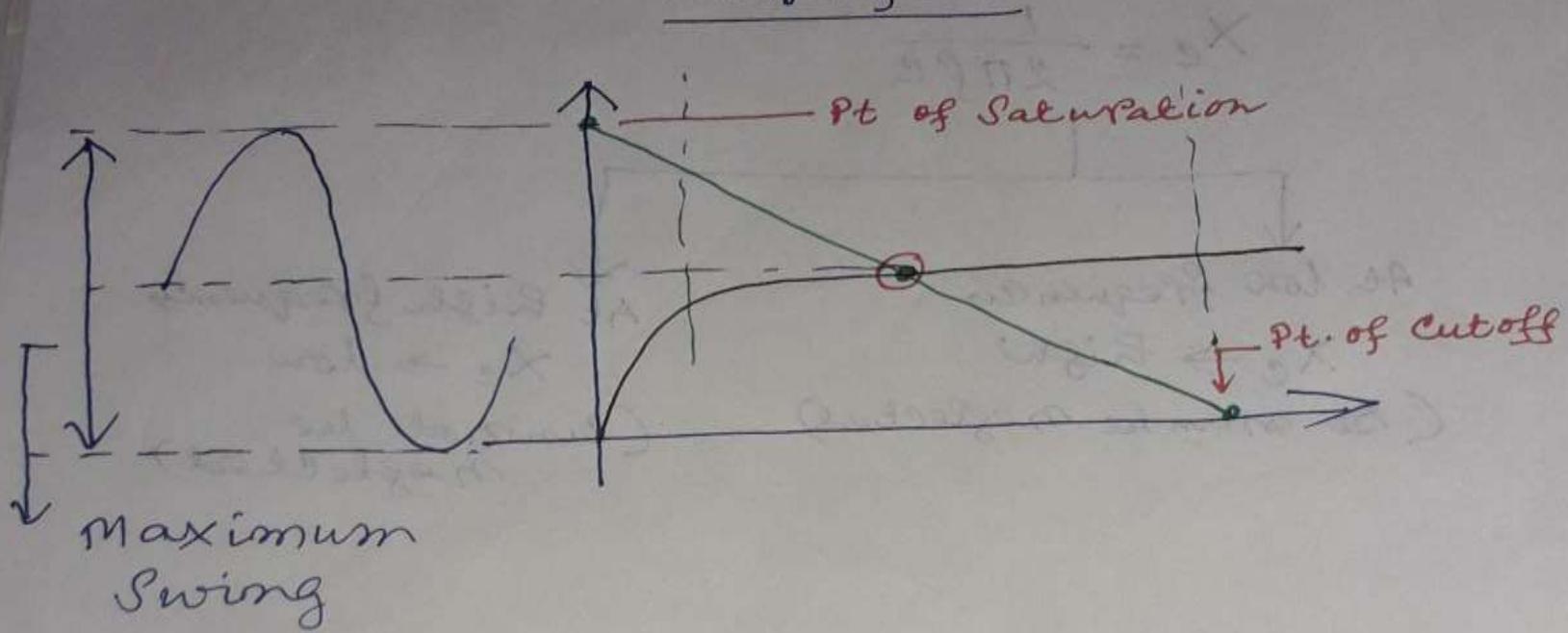
- Low Frequency model  
of Transistor Amplifier
- High Frequency model  
of Transistor Amplifier

Another Consideration.

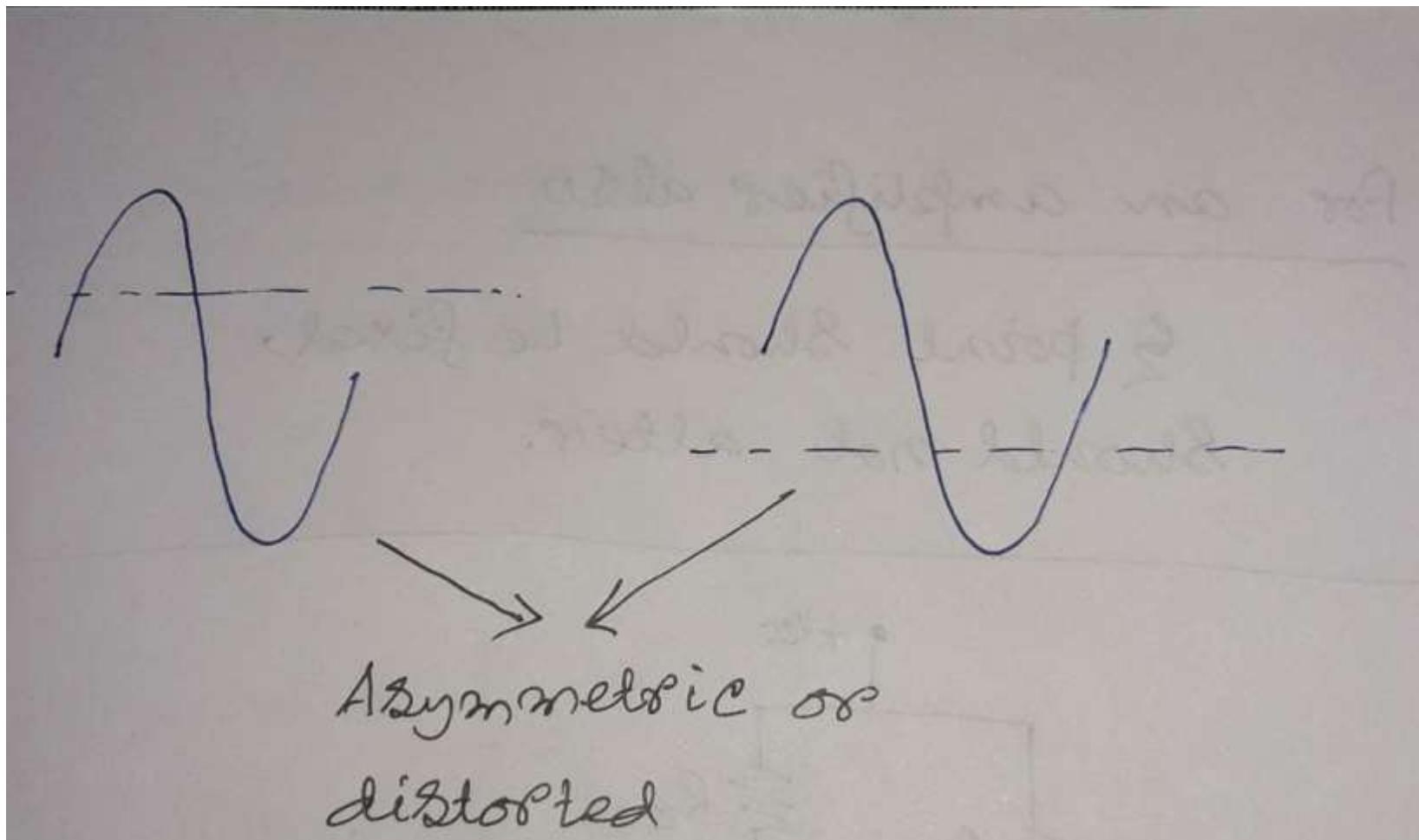
- Small Signal Transistor Amplifier
- Power Transistor Amplifier  
[large signal amplifiers]

# Transistor Amplifier

Position of Q point of  
Amplifier



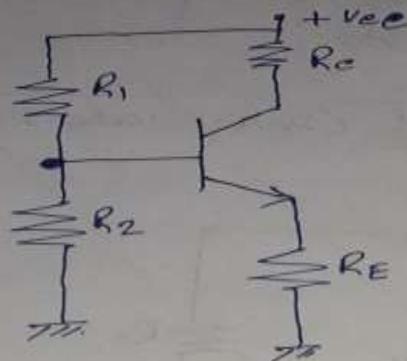
# Transistor Amplifier



# Transistor Amplifier

To get an symmetries.

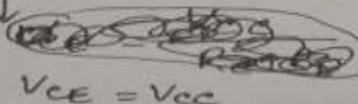
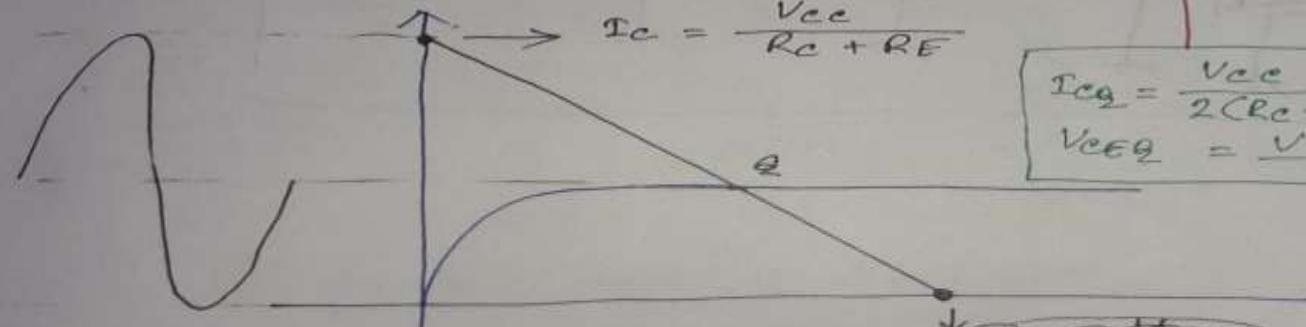
The lease line should pass throw the middle.



Condns for maxm.  
symmetrical  
swing.

$$I_C = \frac{V_{CC}}{R_C + R_E}$$

$$\boxed{I_{CQ} = \frac{V_{CC}}{2(R_C + R_E)} \quad V_{CEQ} = \frac{V_{CC}}{2}}$$

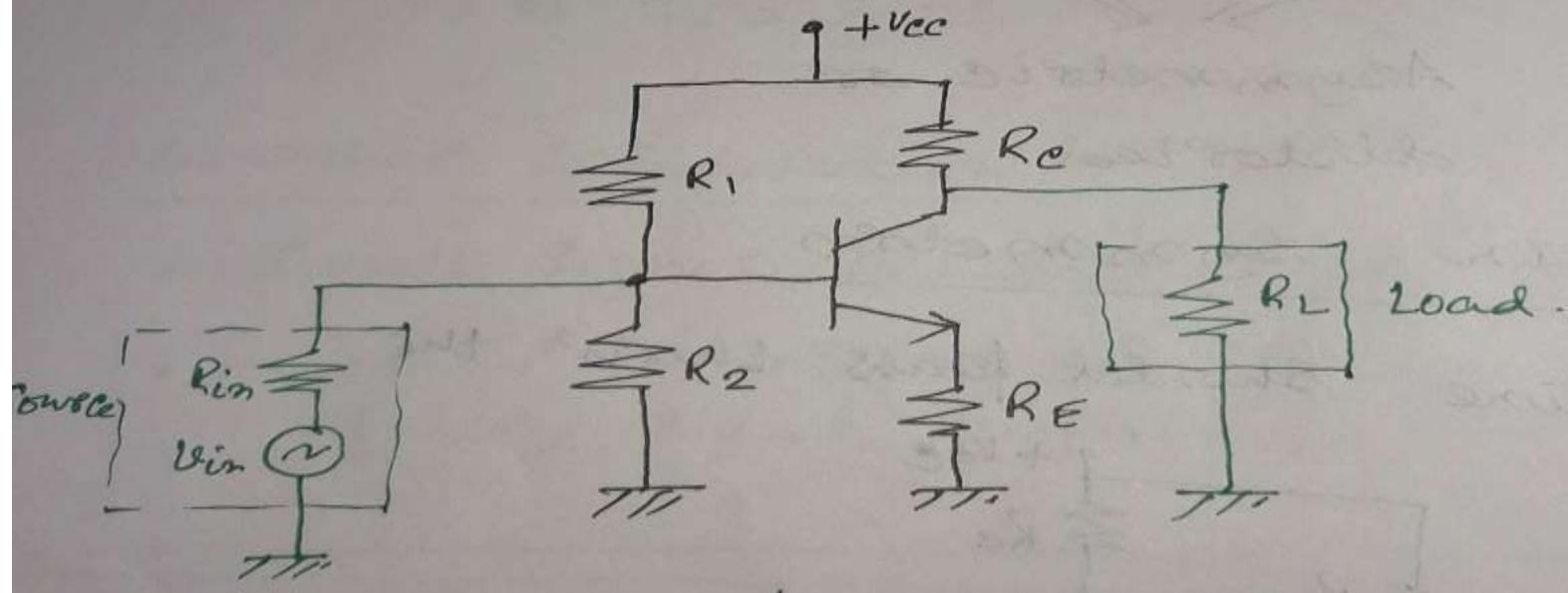


$$V_{CE} = V_{CC}$$

# Transistor Amplifier

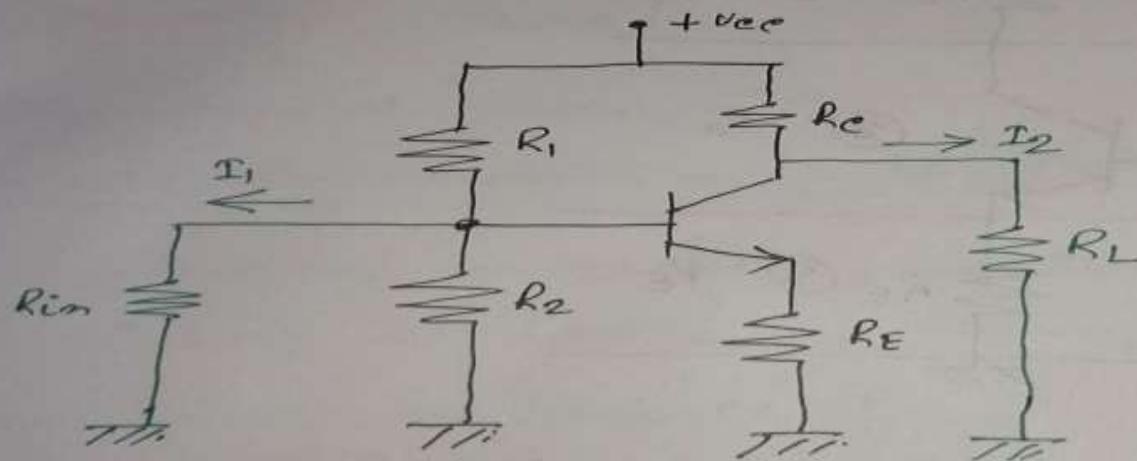
For an amplifier also

Q point should be fixed,  
Should not alter.



# Transistor Amplifier

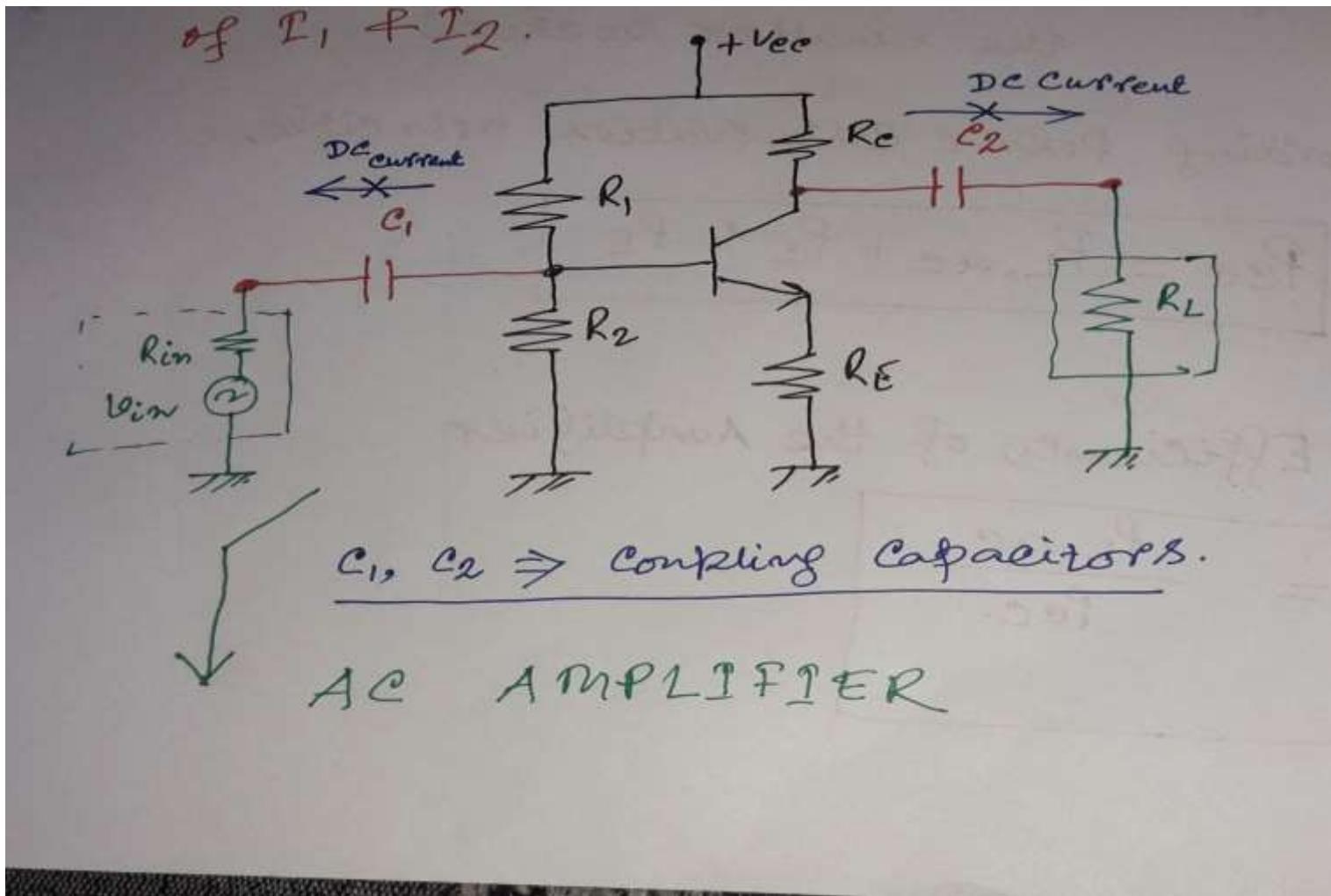
DC Equivalent circuit.



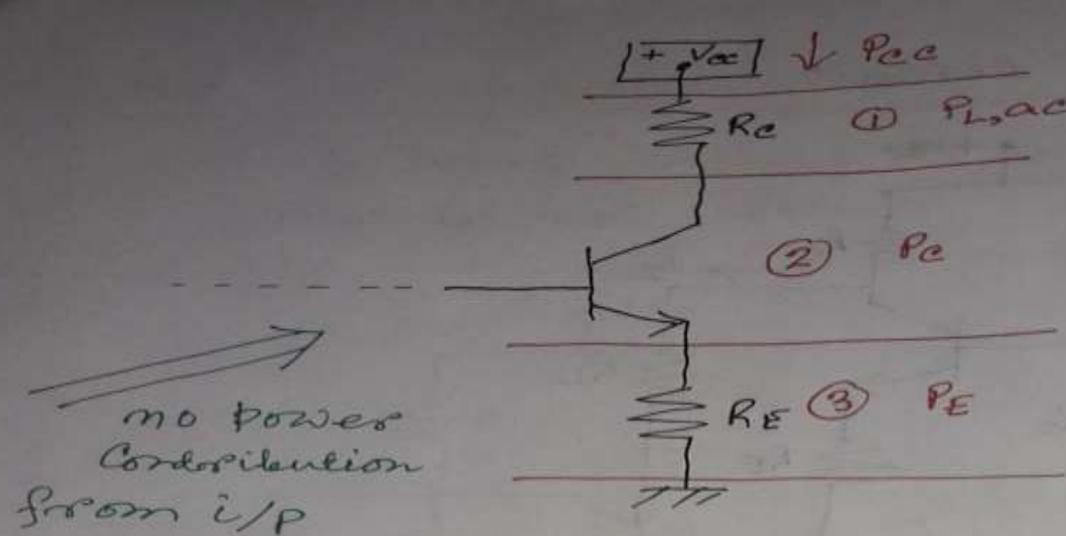
Additional currents ( $I_1, I_2$ ) will cause the change of posn. of Q point.

By some means the posn. of the Q point should be as it is i.e we have to stop the flow of  $I_1 + I_2$ .

# Transistor Amplifier



# Transistor Amplifier



$P_{cc}$  = Power Supplied to Amplifier

$P_{L,ac}$  = Load Power Dissipation

$P_C$  = Load Power Dissipation across  
C-E Junction  
= Conduction Loss

$P_E$  = Power Dissipation in  
the emitter Section

# Transistor Amplifier

According Power Conservation principle,

$$P_{cc} = P_{L,ac} + P_c + P_E$$

$\eta$  = Efficiency of the Amplifier

$$\eta = \frac{P_{L,ac}}{P_{cc}}$$

# Transistor Amplifier

As  $P_{cc}$  is fixed,  $[P_{cc} = V_{cc} \cdot I_{ce}]$

so  $\eta \uparrow$   $P_{L,ac} \uparrow$

we cannot alter  $P_c$ .

So recommendation is to reduce  $P_E$ .

But, according to stability factor analysis.

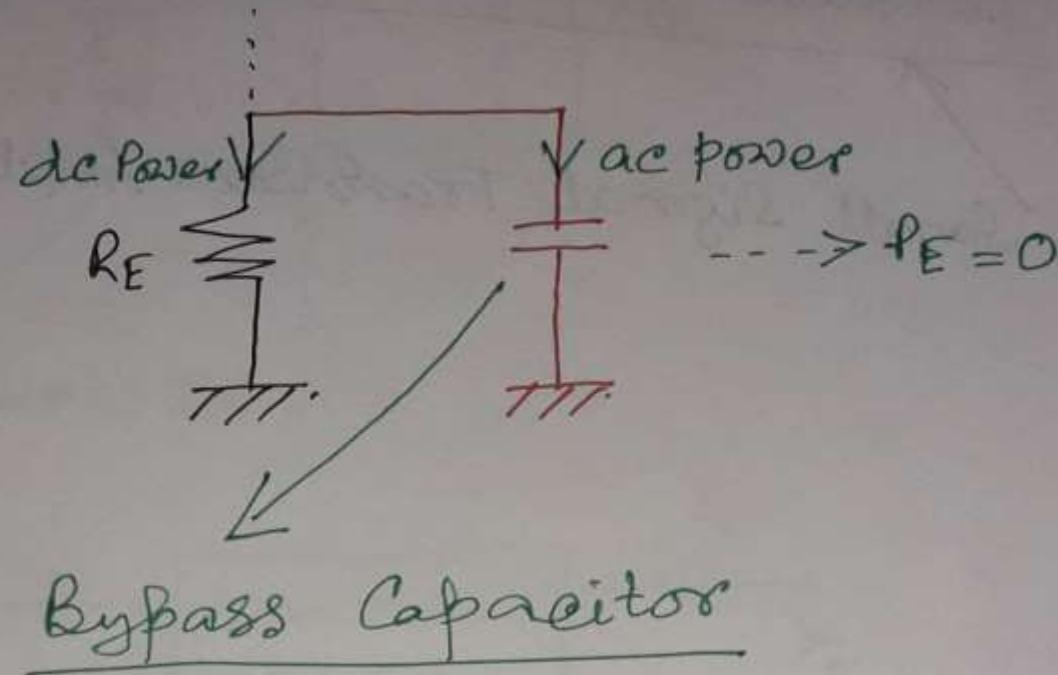
$R_E$  should be large  $[S_V = -\frac{1}{R_E}]$

then how to reduce  $P_E$

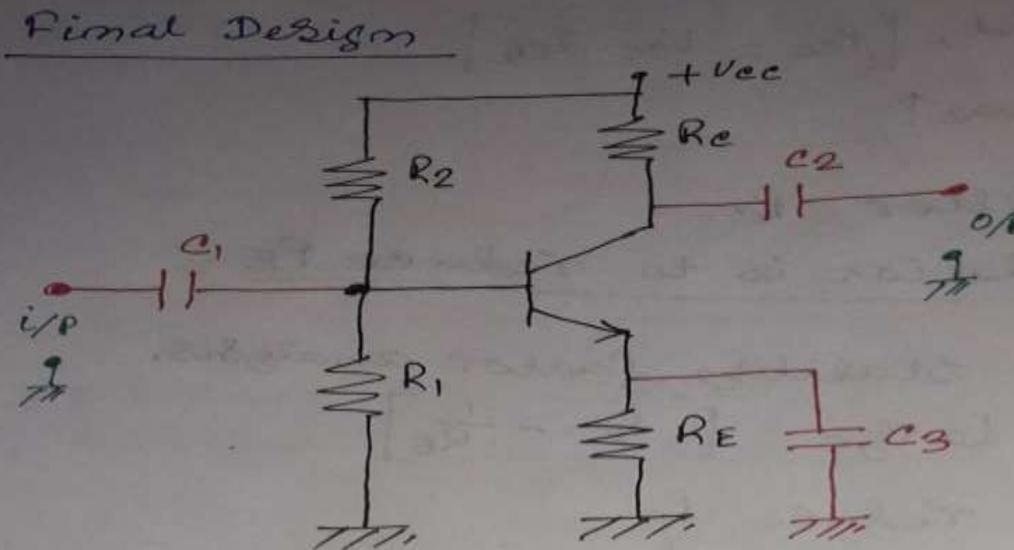
↓  
ac power dissipation  
in the emitter section.

# Transistor Amplifier

Solution:



# Transistor Amplifier



$C_1, C_2 \Rightarrow$  Coupling Capacitor

$C_3 \Rightarrow$  Bypass Capacitor

R-C Coupled Transistor Amplifier

Small Signal Transistor Amplifier

# Transistor Amplifier

## Low Frequency Model

objective - (1) To find out Gain

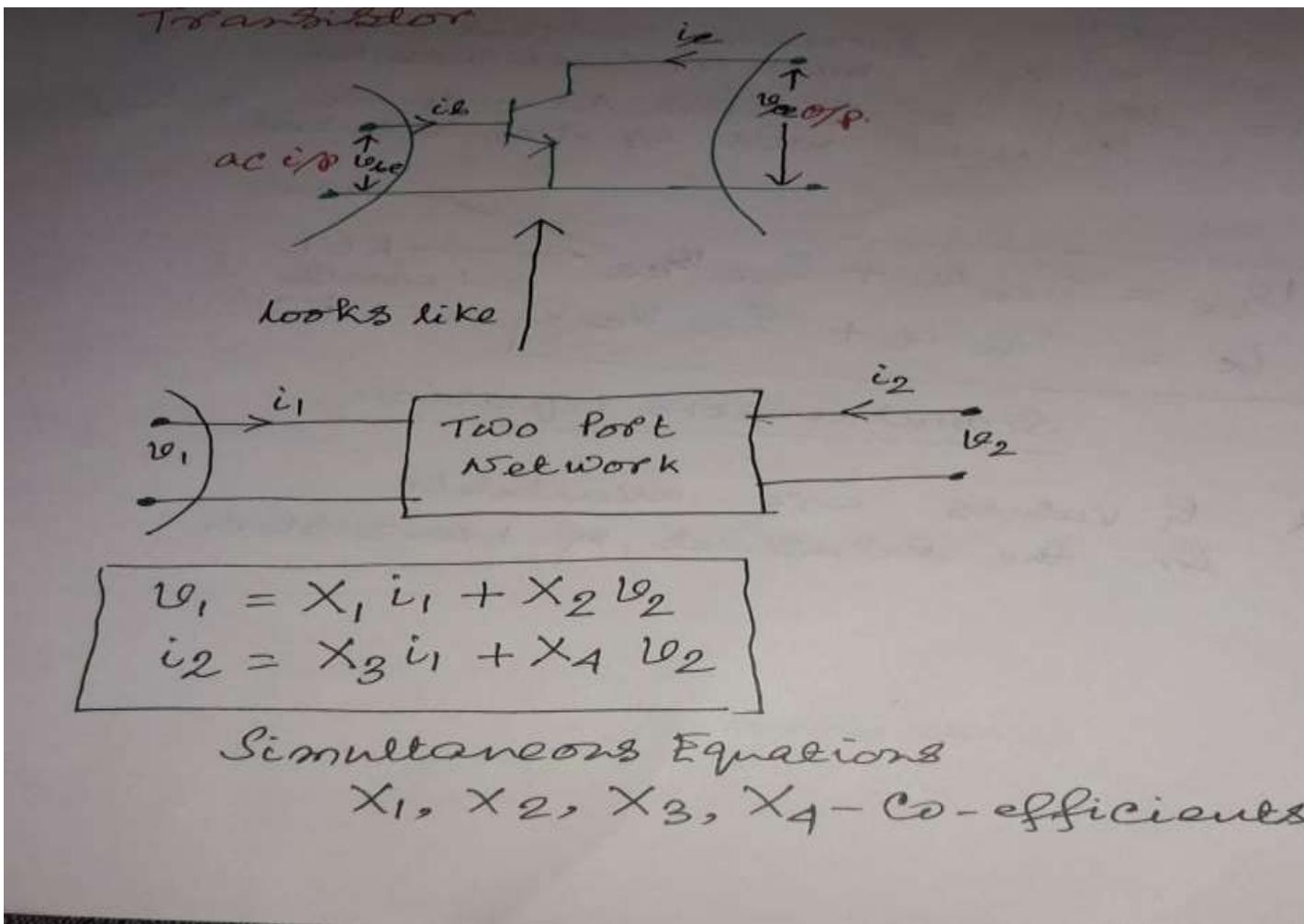
(2) To find out Gain vs. frequency i.e  
frequency response

[helps to get Bandwidth]

- Effect of the internal capacitances are not considered.

>> In the amplifier, frequency response of all components are known except Transistor.

# Transistor Amplifier



# Transistor Amplifier

From fig.

$$v_{o1} = v_{ce}, i_1 = i_b$$

$$v_{o2} = v_{ce} + i_2 = i_e$$

$$\begin{cases} v_{ce} = X_1 i_b + X_2 v_{ce} \\ i_e = X_3 i_b + X_4 v_{ce} \end{cases} \quad \text{--- hybrid parameter}$$

$$X_1 = \left. \frac{v_{ce}}{i_b} \right|_{v_{ce}=0} = \text{Input Impedance with O/P short circuited} = h_{ie}$$

$$X_2 = \left. \frac{v_{ce}}{i_b} \right|_{i_b=0} = \text{Reverse Voltage gain with I/P open circuited} = h_{re}$$

$$X_3 = \left. \frac{i_e}{i_b} \right|_{v_{ce}=0} = \text{Forward current gain with O/P short circuited} = h_{fe}$$

$$X_4 = \left. \frac{i_e}{v_{ce}} \right|_{i_b=0} = \text{Output Admittance with I/P open circuited} = h_{oe}$$

$$\begin{cases} v_{ce} = h_{ie} i_b + h_{re} v_{ce} \\ i_e = h_{fe} i_b + h_{oe} v_{ce} \end{cases} \quad \begin{array}{l} \text{eqn ①} \\ \text{KVL} \end{array} \quad \begin{array}{l} \text{eqn ②} \\ \text{KCL} \end{array}$$

Simultaneous Equation.

- \*  $h$  values are available in the datasheet of transistor.

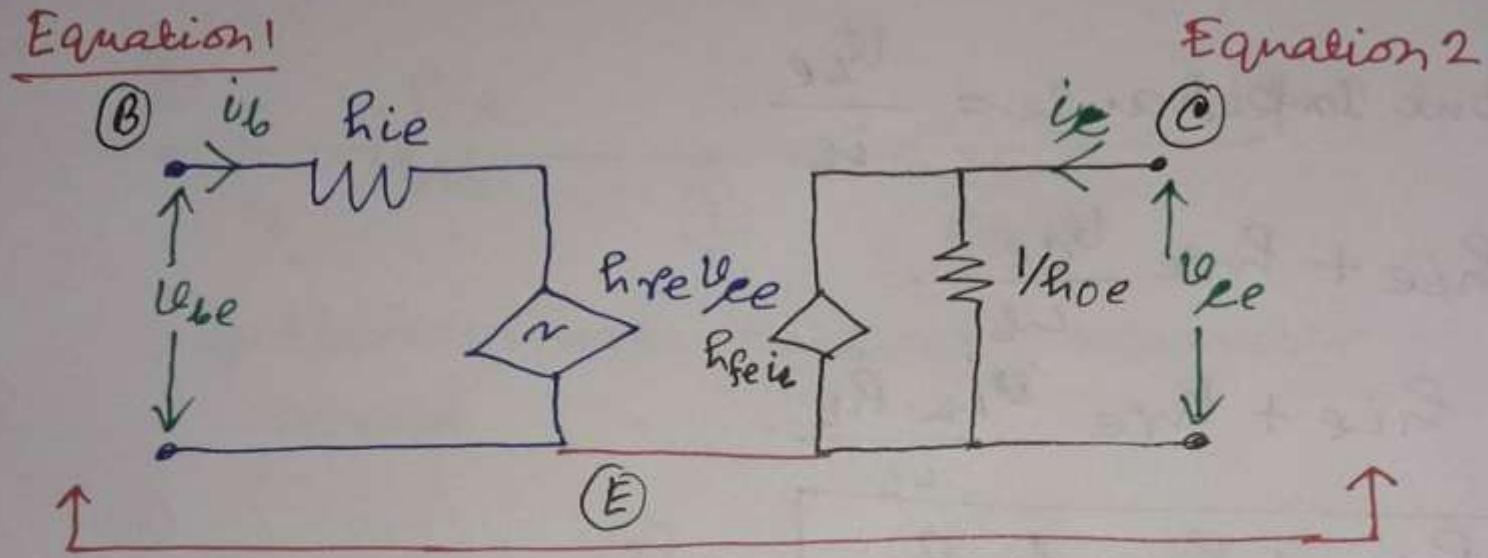
# Transistor Amplifier

$$\begin{aligned} & V_{be} = h_{fe} i_b + h_{oe} V_{ce} \quad \text{KUL} \\ & i_c = h_{fe} i_b + h_{oe} V_{ce} \quad \text{KCL} \end{aligned}$$

Simultaneous Equation.

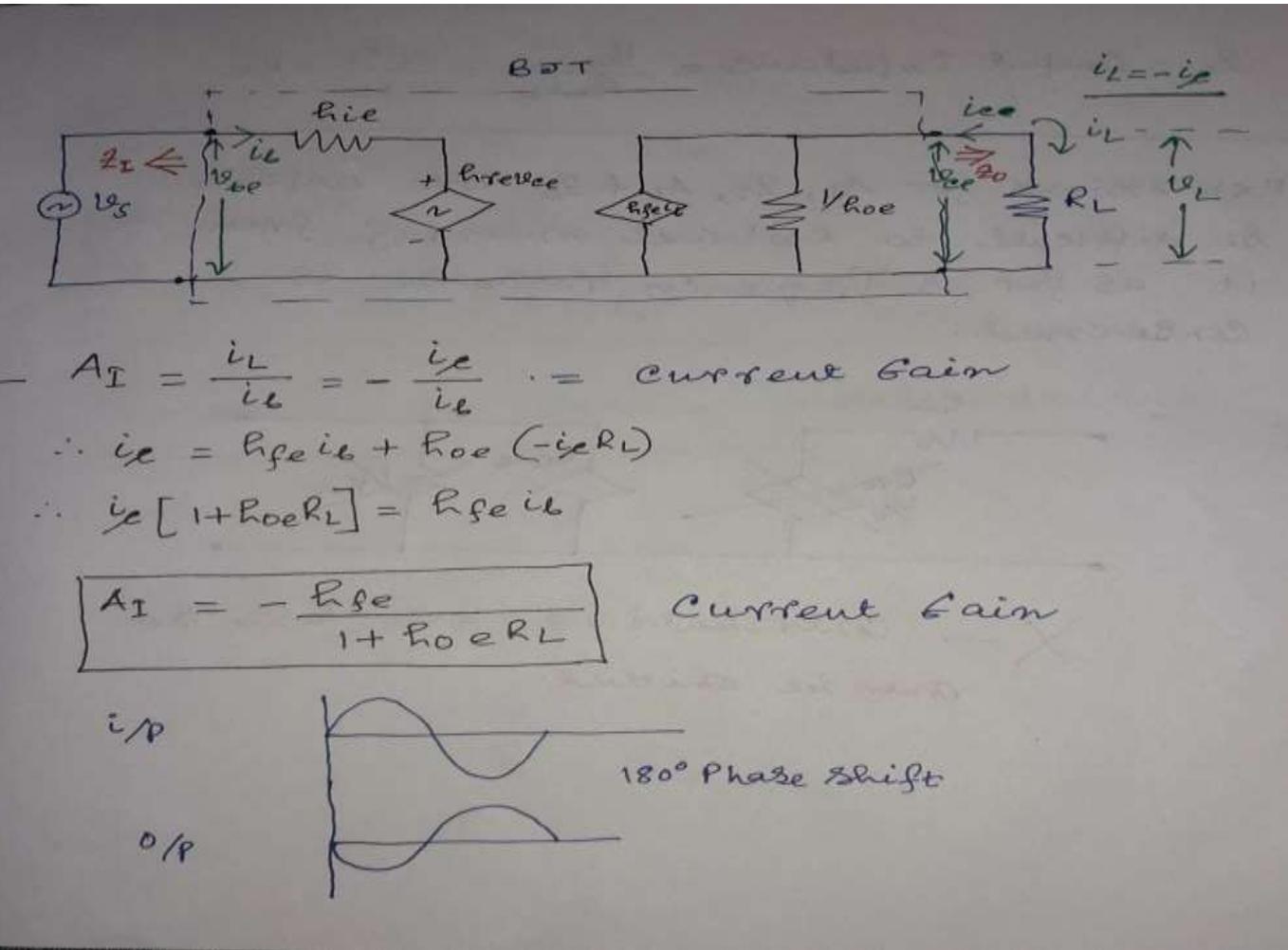
- \*  $h$  values are available in the datasheet of transistor.

# Transistor Amplifier



- BJT represented in low frequency hybrid parameter model.

# Transistor Amplifier



# Transistor Amplifier

$$Z_I = \text{Input Impedance} = \frac{V_{ce}}{i_b} .$$

$$= h_{ie} + h_{re} \frac{V_{ce}}{i_b} .$$

$$= h_{ie} + h_{re} \frac{i_L \cdot R_L}{i_b} .$$

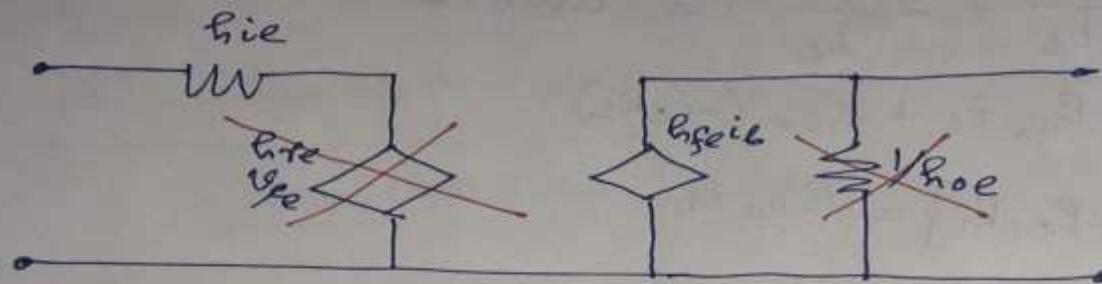
$$\boxed{Z_I = h_{ie} + h_{re} A_I R_L}$$

$$A_V = \text{Voltage Gain} = \frac{V_{ce}}{V_{ee}} = \frac{i_L R_L}{i_e Z_I} = A_I \frac{R_L}{Z_I} .$$

$$Z_O = \text{Output Impedance} = \frac{V_{ce}}{i_L} = \frac{i_L R_L}{i_L} = R_L$$

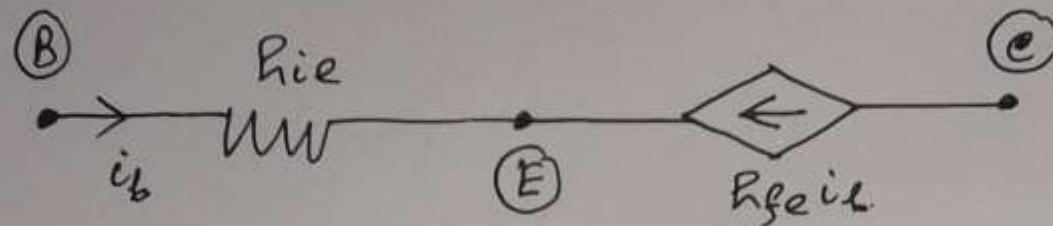
# Transistor Amplifier

Expressions for  $A_I$ ,  $Z_I$ ,  $A_V + Z_0$  are complex.  
So difficult to extract meaning from  
it as far as frequency response is  
concerned.

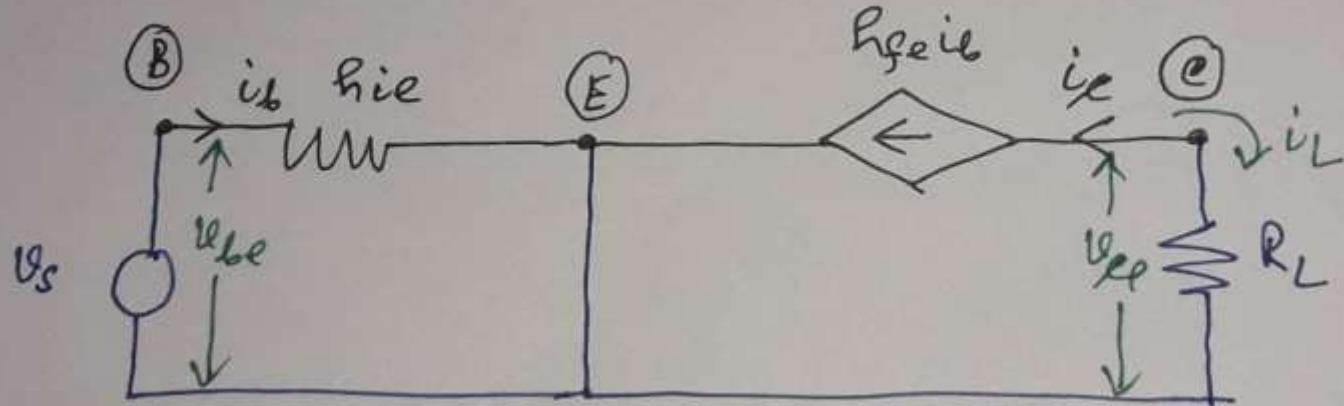


X - Contributions are less, so  
may be omitted.

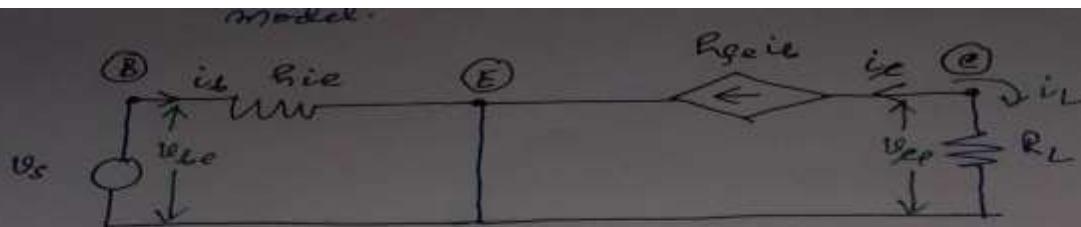
# Transistor Amplifier



→ Approximate hybrid parameter model.



# Transistor Amplifier



$$i_L = -i_e = -r_{ce} i_b.$$

$$A_I = \text{Current gain} = -r_{ce}$$

$$Z_I = \frac{v_{be}}{i_e} = \frac{r_{be} i_b}{i_b} = r_{be}.$$

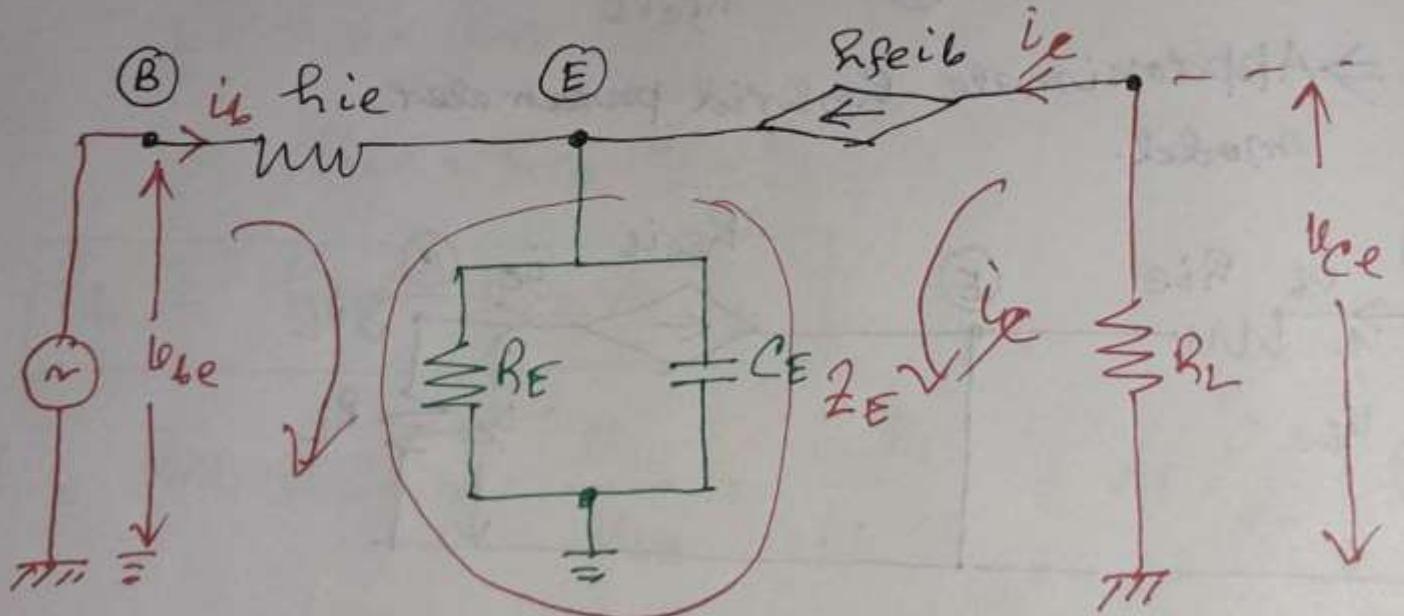
$$Z_O = \frac{v_{ce}}{i_L} = R_L$$

$$A_V = \frac{v_{ce}}{v_{be}} = \frac{i_b R_L}{i_b r_{be}} = A_I \cdot \frac{R_L}{r_{be}}$$

Available in the datasheet, mostly dependent of transistor parameters.

# Transistor Amplifier

Frequency Response of BJT Amplifier  
- Low frequency



# Transistor Amplifier

since  $i_E = h_{FE} i_B$

$$\begin{aligned} V_{BE} &= h_{IE} i_B + i_B Z_E + i_E Z_E \\ &= i_B [h_{IE} + Z_E + h_{FE} Z_E] \\ &= i_B [h_{IE} + Z_E (1 + h_{FE})] \end{aligned}$$

$$\begin{aligned} V_{CE} &= i_L R_L = -i_C R_L \\ &= -h_{FE} i_B R_L \end{aligned}$$

$$A_V = \frac{V_{CE}}{V_{BE}} = -\frac{h_{FE} i_B R_L}{i_B [h_{IE} + Z_E (1 + h_{FE})]} = \frac{\text{Voltage Gain}}{\text{Gain}}$$

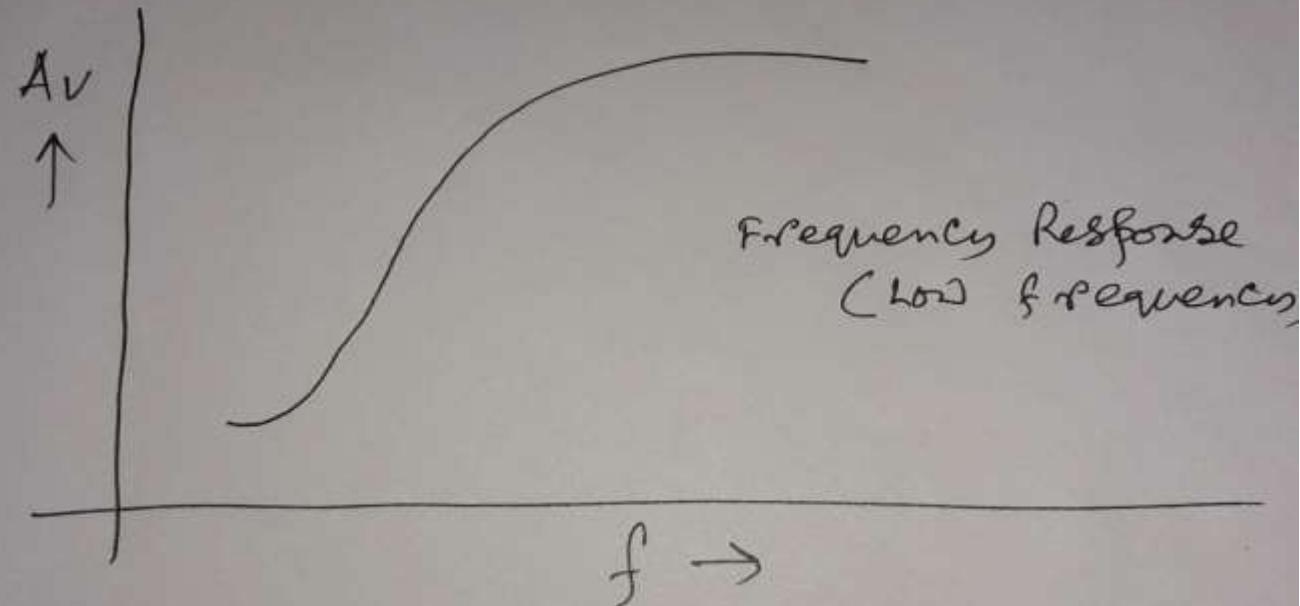
# Transistor Amplifier

$$Z_E = \frac{R_E \cdot \frac{1}{j\omega CE}}{R_E + \frac{1}{j\omega CE} + \frac{R_E / j\omega CE}{j\omega CE R_E + 1}}$$

$$Z_E = \frac{R_E}{1 + j\omega CE R_E}$$

# Transistor Amplifier

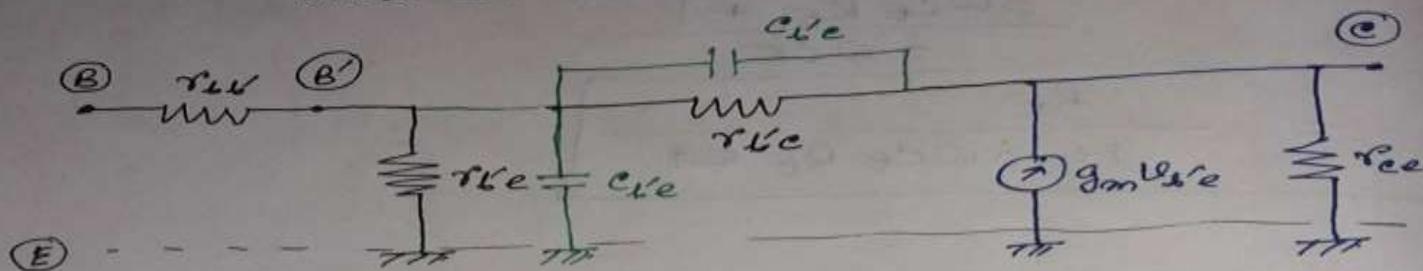
$$A_V = - \frac{h_{fe} R_L}{h_{ie} + \frac{(1+h_{fe}) R_E}{1 + j\omega C_E R_E}}$$



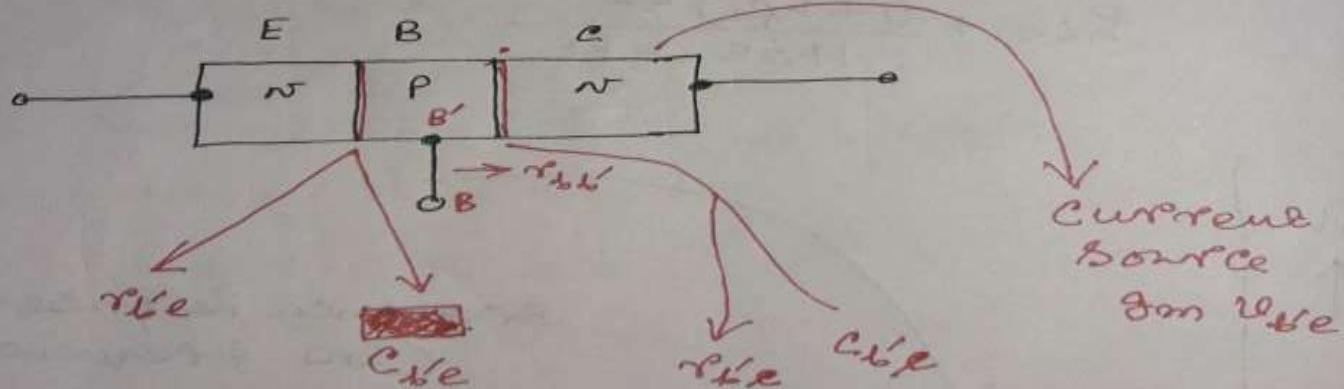
# High Frequency Model

High Frequency model  
of Transistor Amplifier

- Effect of the junction capacitance  
must be considered.



$r_{be}$  = Base Spreading resistance



# High Frequency Model

$r$  Values &  $g_m$  are not available  
in the datasheet.

$$g_m = \text{transconductance} = \frac{i_e}{v_{be}} = \frac{\alpha i_e}{v_{be}'e} .$$
$$= \frac{\alpha}{v_{be}/i_e} = \frac{\alpha}{r_e}$$

$$\boxed{r_e = \frac{25mV}{I_E}}$$

# High Frequency Model

Low Frequency Equivalent of High frequency model

$i_{be} = \frac{v_{be}}{r_{be}} \Big|_{i_b=0} = \frac{r_{be}}{r_{be} + r_{be}}$

 $\therefore 1 + \frac{r_{be}}{r_{be}} = \gamma_{Roe}$ 
 $\therefore \frac{r_{be}}{r_{be}} = \frac{1}{\gamma_{Roe}} - 1 = \frac{1 - \gamma_{Roe}}{\gamma_{Roe}} \approx \frac{1}{\gamma_{Roe}}$ 
 $i_{fe} = \frac{i_e}{i_b} \Big|_{v_{be}=0} = \frac{B_m v_{be}}{v_{be}/r_{be}} \Rightarrow r_{be} = \frac{r_{be}}{B_m}$ 
 $\therefore \boxed{r_{be} = \frac{r_{fe}}{\gamma_{Roe} \cdot B_m}}$

# High Frequency Model

$$r_{bb'} + r_{b'e} = \text{hie}$$

$$\therefore r_{bb'} = \text{hie} - r_{b'e} \Rightarrow r_{bb'} = \text{hie} - \frac{r_{fe}}{g_m}$$

# High Frequency Model

$$i_e = g_m v_{be} + \frac{v_{ce}}{r_{be} + r_{bf}} + \frac{v_{ce}}{r_{ce}} .$$

$$\therefore \frac{i_e}{v_{ce}} \Big|_{i_e=0} = h_{oe} = g_m h_{fe} + \frac{1}{\frac{h_{fe}}{g_m} + \frac{h_{fe}}{g_m h_{fe}}} + \frac{1}{r_{ce}} .$$

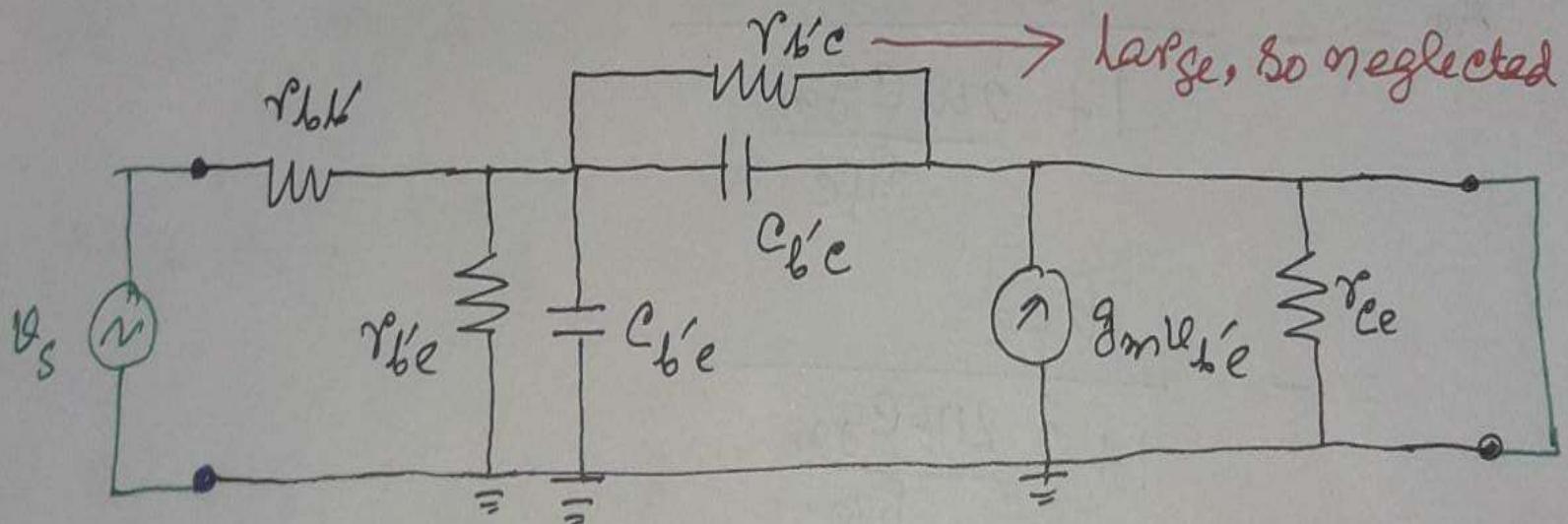
$$\therefore \frac{1}{r_{ce}} = h_{oe} - \left\{ g_m h_{fe} + \frac{g_m}{h_{fe} \left( \frac{1+h_{fe}}{h_{fe}} \right)} \right\}$$

$$= h_{oe} - \left\{ g_m h_{fe} + \frac{g_m h_{fe}}{h_{fe}} \right\}$$

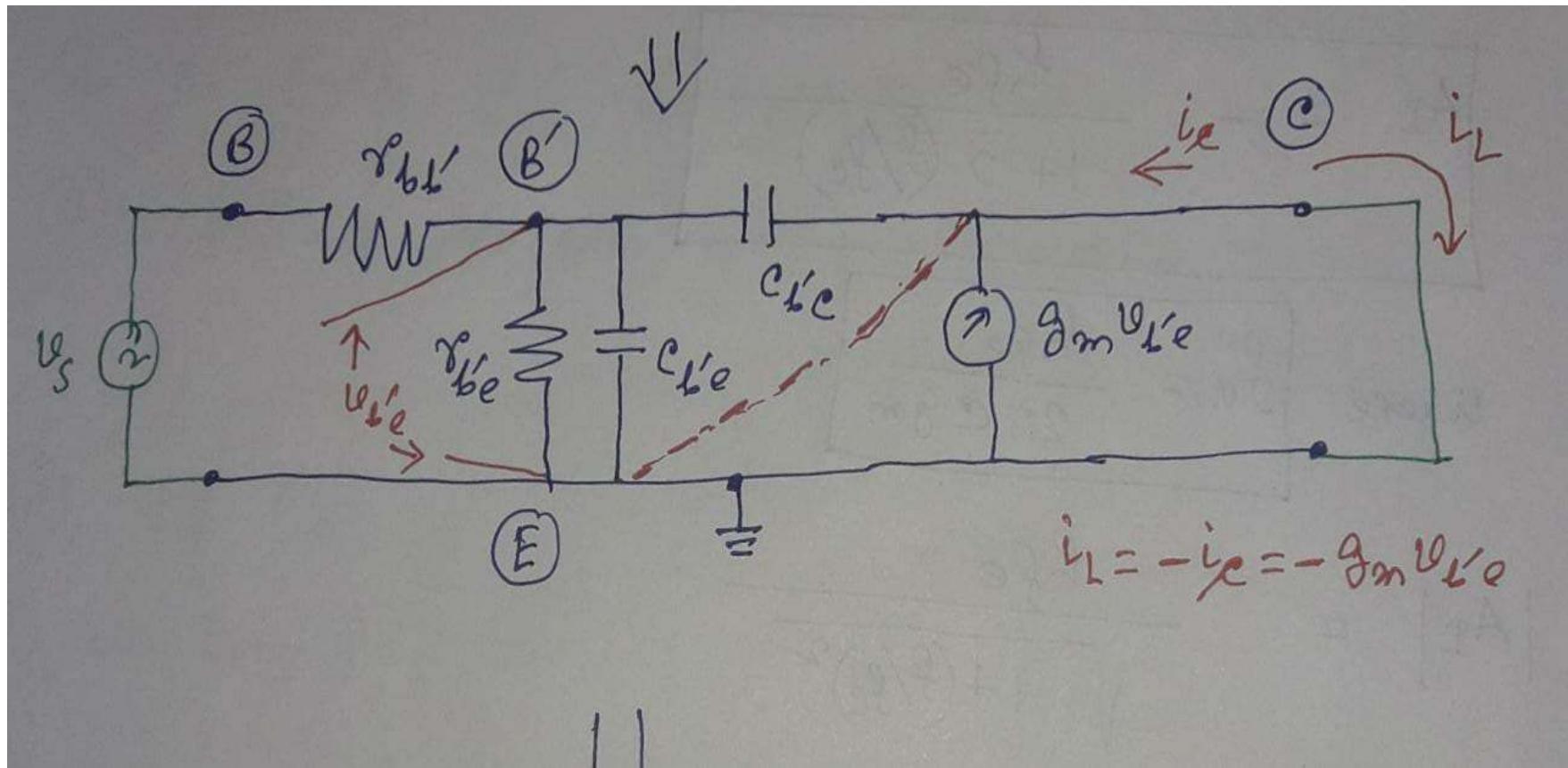
$$r_{ce} = \boxed{\left[ h_{oe} - g_m h_{fe} - \frac{g_m h_{fe}}{h_{fe}} \right]^{-1}}$$

# High Frequency Model

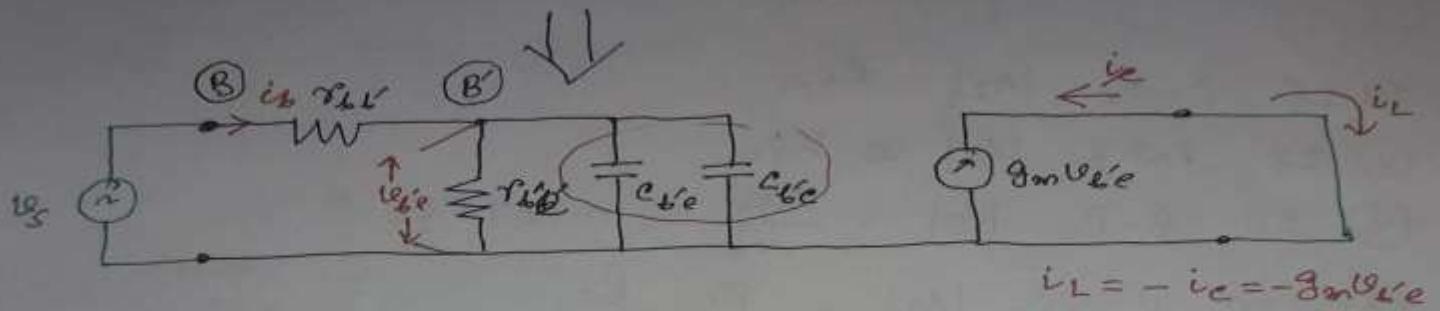
Frequency Response When O/P Short Circuited



# High Frequency Model



# High Frequency Model



$$C = C_{L'e} + C_{L'e}$$

$$\begin{aligned} i_L &= v_{L'e} \left[ \frac{1}{r_{L'e}} + j\omega C \right] \\ &= v_{L'e} \left[ \frac{g_m}{R_{L'e}} + j\omega C \right] \end{aligned}$$

$$\therefore A_T = \frac{i_L}{i_S} = - \frac{g_m v_{L'e}}{v_{L'e} \left[ \frac{g_m}{R_{L'e}} + j\omega C \right]}$$

# High Frequency Model

$$A_I = - \frac{h_{fe}}{1 + j \omega C \cancel{R_{ce}} \frac{h_{fe}}{B_R g_m}}$$

$$= - \frac{h_{fe}}{1 + j \frac{2\pi f C \cancel{R_{ce}} h_{fe}}{B_R g_m}}$$

$$\boxed{A_I = - \frac{h_{fe}}{1 + j (\frac{f}{f_c})}}$$

where

$$f_c = \frac{B_R g_m}{2\pi C h_{fe}}$$

$$f_c = \frac{g_m}{2\pi C h_{fe}}$$

$$|A_I| = \frac{h_{fe}}{\sqrt{1 + (\frac{f}{f_c})^2}}$$

# High Frequency Model

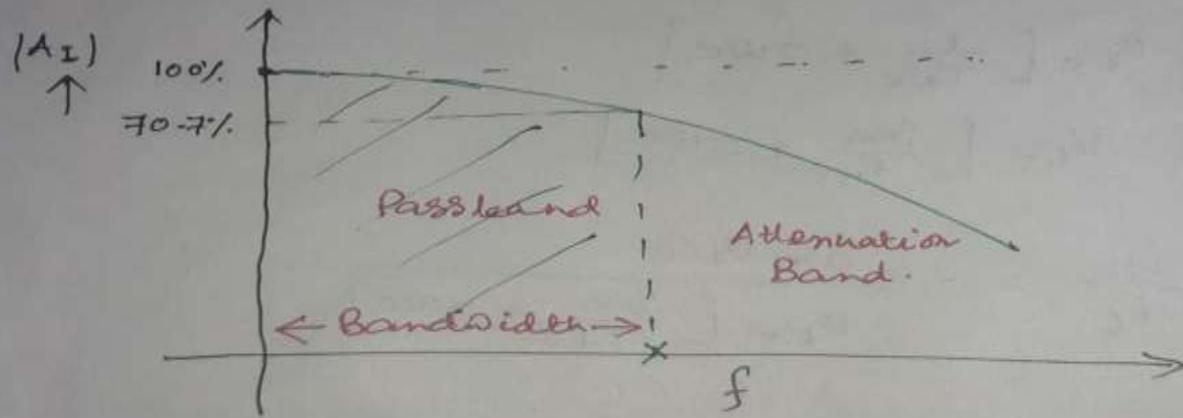
$$|A_T| = \frac{R_{fe}}{\sqrt{1 + (f/f_c)^2}}$$

① If  $f = 0$ ,  $|A_T| = R_{fe}$

② If  $f \ll f_c$   $|A_T| \approx R_{fe}$

③ If  $f = f_c$   $|A_T| = \frac{R_{fe}}{\sqrt{2}} = 0.707 R_{fe}$

④ If  $f \gg f_c$   $|A_T| = R_{fe} \cdot \frac{f_c}{f}$



# High Frequency Model

As  $|A_I|$  is a large quantity, normally it is expressed in terms of dB.

$$|A_I| \text{ in dB} = 20 \log_{10} |A_I|$$

① If  $f=0$ ,  $|A_I| \text{ in dB} = 20 \log_{10} f_{fe} \dots \text{(maxm)} \dots 0 \text{ dB}$

② If  $f \ll f_c$ ,  $|A_I| \text{ in dB} \approx 20 \log_{10} f_{fe} \dots$

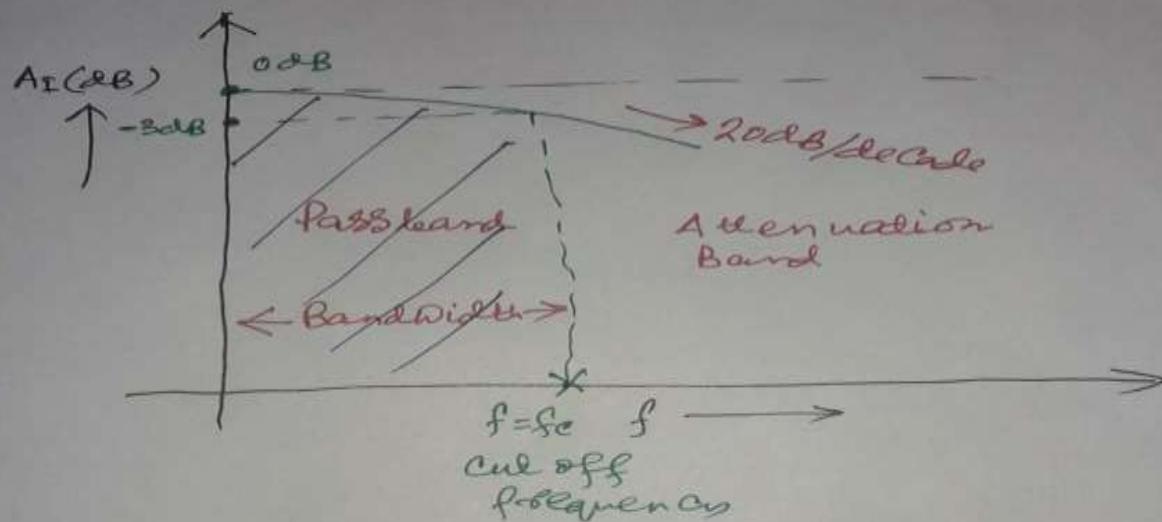
③ If  $f=f_c$   $|A_I| (\text{dB}) = 20 \log_{10} f_{fe} - 20 \log_{10} \sqrt{2}$   
 $= 0 \text{ dB} - 3 \text{ dB} = -3 \text{ dB}$

# High Frequency Model

① If  $f \gg f_c$

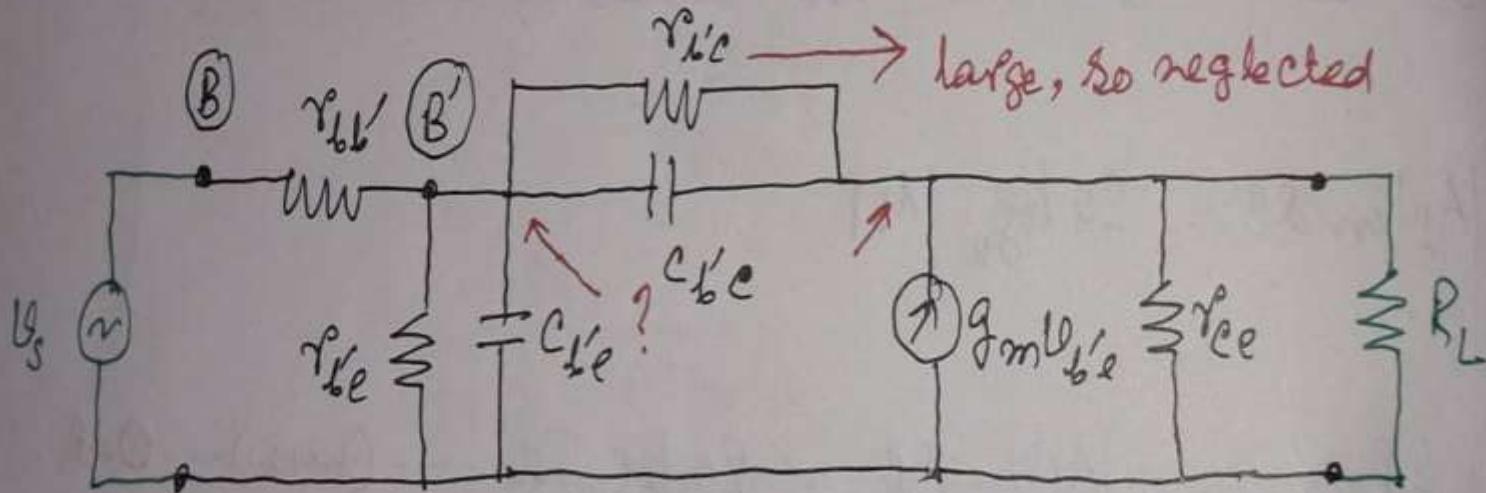
lets say  $f = 10 f_c$ .

$$A_2(\text{in dB}) = 20 \log_{10} f/f_c - 20 \log_{10} 10 \\ = -20 \text{ dB.}$$

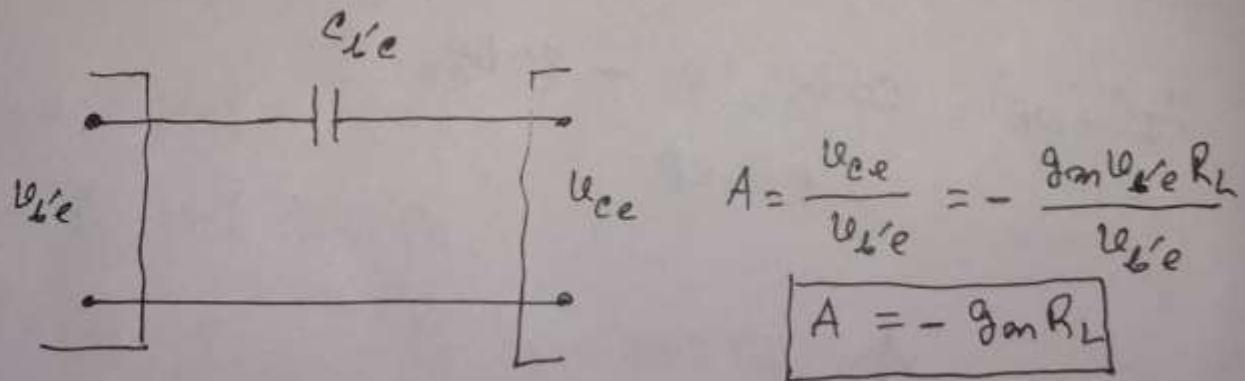
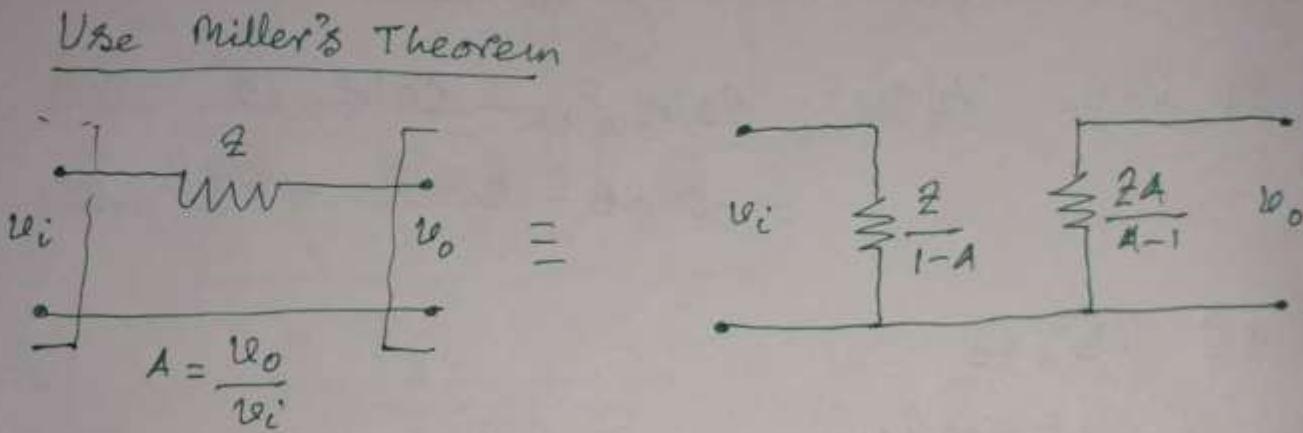


# High Frequency Model

Frequency Response When  $R_L$  is Connected at the load



# High Frequency Model



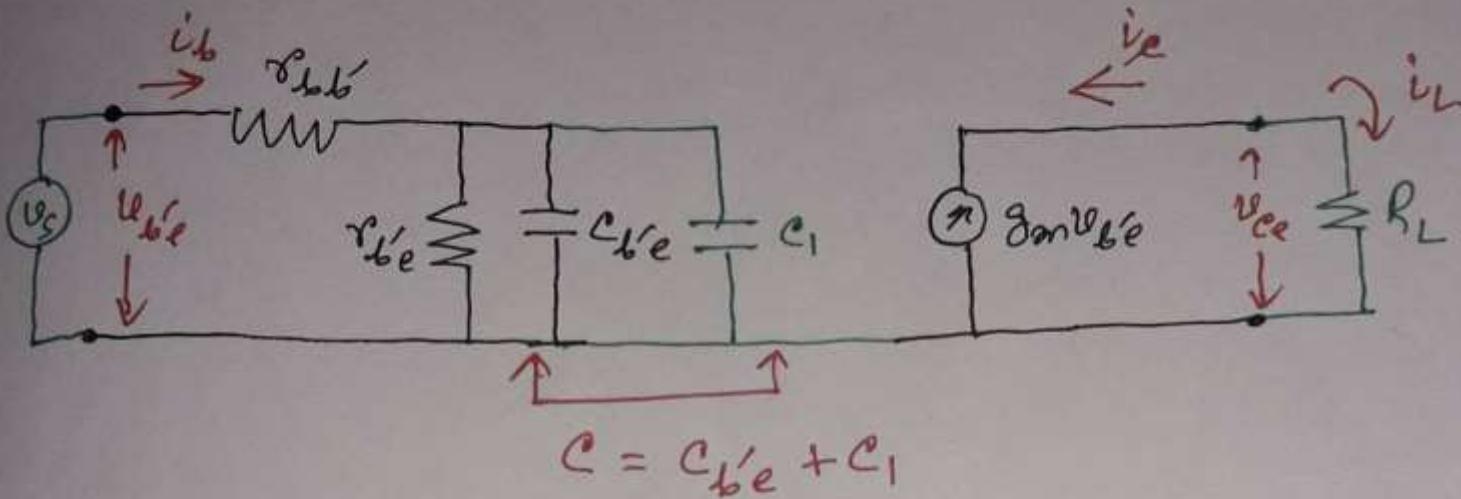
# High Frequency Model

$$\frac{Z}{1-A} = \frac{\frac{1}{j\omega C_L'c}}{1 + g_m R_L} = \frac{1}{j\omega C_L'c (1 + g_m R_L)}$$
$$= \frac{1}{j\omega C_1}$$

where  $C_1 = C_L'c (1 + g_m R_L)$

$$\frac{ZA}{A-1} = \frac{(-g_m R_L) \frac{1}{j\omega C_L'c}}{-g_m R_L - 1} \approx \frac{1}{j\omega C_L'c}$$

# High Frequency Model



$$\begin{aligned} i_b &= v_{be}' \left[ \frac{1}{r_{be}'} + j\omega C \right] \\ &= v_{be}' \left[ \frac{\beta_m}{R_{fe}} + j\omega C \right] \end{aligned}$$

# High Frequency Model

$$A_T = \frac{v_L}{i_L} = \frac{-g_m v_{be}}{v_{be} \left[ \frac{g_m}{R_{fe}} + j\omega_c \right]}$$
$$= - \frac{R_{fe}}{1 + \frac{j\omega_c R_{fe}}{g_m}}$$

$$\boxed{A_T = - \frac{R_{fe}}{1 + j\left(\frac{f}{f_c}\right)}}$$

where  $f_c = \frac{g_m}{2\pi C R_{fe}}$

$$\boxed{C = C_{be} + C_{bc} (1 + g_m R_L)}$$

# High Frequency Model

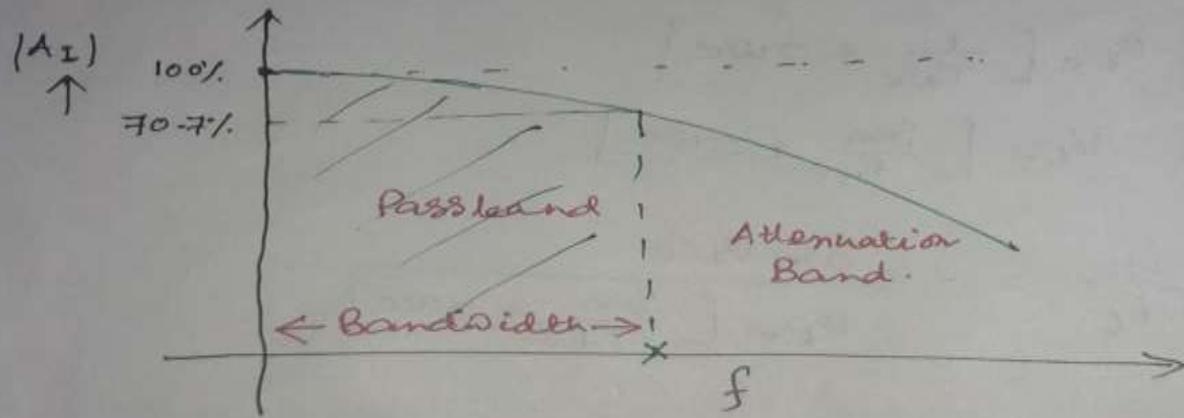
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① If  $f=0$ ,  $|A_I| \text{ in dB} = 20 \log_{10} f_{fe} \dots \text{(maxm)} \dots 0 \text{ dB}$

② If  $f \ll f_c$ ,  $|A_I| \text{ in dB} \approx 20 \log_{10} f_{fe} \dots$

③ If  $f=f_c$   $|A_I| (\text{dB}) = 20 \log_{10} f_{fe} - 20 \log_{10} \sqrt{2}$   
 $= 0 \text{ dB} - 3 \text{ dB} = -3 \text{ dB}$

# High Frequency Model

① If  $f \gg f_c$

lets say  $f = 10 f_c$ .

$$A_2(\text{in dB}) = 20 \log_{10} f/f_c - 20 \log_{10} 10 \\ = -20 \text{ dB.}$$

